

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Inventor: TZU YU WANG) Confirmation No. 1061
Serial No: 10/656,224) Art Unit: 2823
Filed: September 8, 2003) Examiner: Brook Kebede
Title: METHOD FOR SUPPRESSING BORON PENETRATION BY IMPLANTATION IN P+ MOSFETS)))

SUBMISSION OF REVOCATION OF POWER OF ATTORNEY AND GRANT OF POWER OF ATTORNEY

Assistant Commissioner of Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Applicants hereby submit the attached Revocation of Power of Attorney and Grant of Power of Attorney in the above-identified application. Should there be any questions with respect to this submission a representative of the Patent Office is requested to contact the undersigned.

Respectfully submitted,

Registration No. 44,615

TZU YU WANG

Date: February 10, 2005

By:

Poh C. Chua

SHAW PITTMAN LLP 1650 Tysons Boulevard McLean, VA 22102-4859

703-770-7900

PCC/lrhj

Customer No. 28970



PATENT Customer No. 28970

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Patent Application and Patent Numbers:

See attached "Schedule A"

REVOCATION OF POWER OF ATTORNEY AND GRANT OF NEW POWER OF ATTORNEY

The undersigned, a representative authorized to sign on behalf of the assignee owning all of the interest in the listed and pending patent applications and issued patents on the attached sheet (Schedule A), hereby revokes all previous powers of attorney or authorization of agent granted in these patents before the date of execution hereof and appoints all the attorneys associated with Customer Number 28970.

Correspondence in this matter should be directed to:

Yitai Hu SHAW PITTMAN LLP 1650 Tysons Boulevard McLean, Virginia 22102 Telephone: (703) 770-7900 Fax (703) 770-7901

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SCHEDULE A

SERIAL NUI	MBER FILING DATE	THE THE	PATENT NUM	BER ISSUE DATE
		Ono Interpoly Dielectric Flor Flash		
		Memory Cells and Method for		
1		Fabricating The Same Using a		
		Single Wafer Low Temperature		
10/237,668	9/10/2002	Deposition Process	6,777,764	8/17/2004
		Method for Removing Fences		57.172001
		Without Reduction of Ono Film		
10/230,328	8/29/2002	Thickness	6,677,255	1/13/2004
		Programming A Flash Memory	5,6,200	1110/2004
10/230,666	8/29/2002	Cell	6,760,257	7/6/2004
,			0,700,207	170/2004
		Apparatus and Method for		
10/426,833	5/1/2003	Inhibiting Dummy Cell Over Erase	6 787 860	9/7/2004
10.150,000	0,1,2000	This is a second of the second	0,707,000	9/1/2004
		Protection Layer to Prevent Under-		
10/076,629	2/19/2002	Layer Damage During Deposition		6/2/2002
10/010,020	2/10/2002	Sensing Method for EEPROM	6,573,177	6/3/2003
10/151,150	5/21/2002	Refresh Scheme	6 630 930	10/00/0000
10,101,100	0/2 1/2002	Semiconductor Device with	6,639,839	10/28/2003
		Minimal Short-Channel Effects and	ł	
10/101,930	3/21/2002	Low Bit-Line Resistance		4/00/0000
10/101,930	3/2 1/2002		6,555,844	4/29/2003
10/101,922	2/21/2002	Sonos Component Having High	0 400 077	1.0.0
10/101,922	3/21/2002	Dielectric Property	6,498,377	12/24/2002
10/101,931	2/24/2002	Method for Forming An Oxide	0.554.000	
10/101,931	3/21/2002	Layer on a Nitride Layer	6,551,879	4/22/2003
10/186,619	בססביבוד	Structure for Preventing Salicide	0.077.400	
10/ 100,019	7/2/2002	Bridging and Method Thereof	6,677,199	1/13/2004
10/122 206	4/26/2002	Method of Preventing Tungsten		
10/132,286	4/26/2002	Plugs From Corrosion	6,703,301	3/9/2004
10/107 906	7/40/0000	Method for Forming A Phase		
10/197,896	7/19/2002	Change Memory	6,759,267	7/6/2004
10/044 770	0.10.10000	Memory Device and Operation		
10/214,770	8/9/2002	Thereof	6,788,602	9/7/2004
10/047 077		Method for Forming A Phase		
10/847,277	5/17/2004	Change Memory	N/A	NA
10/170 005	0.04.0000	Neural Network for Determining		
10/176,065	6/21/2002	the Endpoint in a Process	N/A	NA
40,007,400		Photoresist Pump Dispense		
10/387,489	3/14/2003	Detection System	N/A	NA
		Cleaning Systems With Monitaring		
10/439,014	5/16/2003	Functions	N/A	NA
10/600,700	6/23/2003	Peer Version Control System	N/A	NA
10/667,447	9/23/2003	Batch Order Change System	N/A	NA
		Elimination of the Fast-Erase		
10/733,230	12/12/2003		N/A	NA
		Cleaning Method Using Ozone DI		
10/731,150	12/10/2003	Process	N/A	NA
		Endpoint Detection in		
		Manufacturing Semi-Conductor		

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		Program/Erase Method for P-		
		Channel Charge Trapping Memory		
10/857,866	6/2/2004	Device	N/A	NA
·	·	Method for Reducing Dimensions		
40405 050	6/20/2002		NI/A	INIA I
10/465,852	6/20/2003	Between Patterns on a Hardmask	N/A	NA
·		Method for Reducing Dimensions		
40/720 040	12/19/2003	Between Patterns on a Photoresist	N/A	NA
10/739,049	12/19/2003	Structure for Preventing Salicide	IN/A	INA
10/673,359	9/30/2003	Bridging and Method Thereof	N/A	NA
10/07 3,339	9/30/2003	Non-Volatile Memory Cell and		INA
10/873,142	1/14/2004	Operating Method	N/A	NA
10/073,142	1714/2004	Memory Device With Built-In Error-	14// \	100
10/237,082	6/2/2003	Correction Capabilities	N/A	NA
10/207,002	0/2/2000	Memory Device With Built-In Error-		
10/449,590	6/2/2003	Correction Capabilities	N/A	NA
10/440,000	0/2/2000	Semi-Conductor Device With		14/1
		Minimal Short-Channel Effects and		
10/361,681	2/11/2003	Low Bit-Line Resistance	N/A	NA
10/00//,00/		Method of Forming a Polysilicon		
		Layer Compressing		
10/715,558	11/19/2003	Microcrystalline Grains	N/A	NA
10/414,048	4/16/2003	ONO Dielectric for Memory Cells	N/A	NA
		•		
	·	Method of Integrating The		ļ
		Fabrication Process for Integrated		
10/418,121	4/18/2003	Circuits and Mem Devices	N/A	NA ·
		Method for Controlling a Butterfly		
10/387,487	3/14/2003	Valve	N/A	NA
10/653,892	9/4/2003	A Non-Volatile Flash Memory	N/A	NA
		Fabrication Method of Sub-		
		Resolution Pitch for Integrated		
10/703,453	11/10/2003	Circuits	N/A	NA
	1011010001	Method for Reducting Dimensions	l	1
09/978,546	10/18/2001	Between Patterns on a Photoresist	N/A	NA
401477 445	0/04/0000	Method for Eliminating Standing		 ,,,
10/177,145	6/24/2002	Waves in a Photoresist Profile	N/A	NA
		Method for Detecting Solvent		İ
40/044 400	0/40/0000	Leakage During Manufacture of a	N/A	l _{NIA}
10/241,486	9/12/2002	Semi-Conductor Device	N/A	NA
40/002 207	0/20/2002	Memory Device and Method of	N/A	l _{NIA}
10/223,327	8/20/2002	Manufacturing The Same Method of Fabricating ONO	N/A	NA
		Dielectric for Non-Volatile		
10/376,225	3/3/2003	Memories	N/A	NA
10/3/0,220	3/3/2003	Method of Forming An Embedded	''\'\	1,10
10/387,488	3/14/2003	ROM	N/A	NA
10/307,400	0/14/2003	Defect Reduction Using Pad	127	1170
10/681,099	10/9/2003	Conditioner Cleaning	N/A	NA
10/001,033	10/3/2003	Toolining	114/7	Lista

SERIAL NUMBER	FILING DATE	THE STATE	PATENT NUMBER	ISSUE DATE
		Method of Preventing Over-Erase		
		of Memory Devices		
		Method for Eliminating Standing		
10/176,061	6/21/2002	Waves in a Photoresist Profile	N/A	NA
		Self-Aligned Patterning in Dual	-	
10/076,630	2/19/2002		N/A	NA
		Method for Forming Tungsten		
		Plugs to Prevent Corrosion		
10/137,406	5/3/2002	Complexity	N/A	NA
		Method for Forming Self-Aligned		
10/186,892	7/2/2002	Salicides	N/A	NA
		Method for Reduced Photoresist		
10/210,032	8/2/2002	Usage	N/A	NA
		Method of Forming Self-Aligned		
10/403,060	4/1/2003		N/A	NA
		Method for Suppressing Boron		
		Penetration by Implantation in P*		
10/656,224	9/8/2003	Mosfets	N/A	NA
		Non-Volatile Memory Cell and		
10/756,777	1/14/2004	Operating Method	N/A	NA
		Sub-90nm Space and Hole		
		Patterning Using 248nm		
	ļ	Lithography with Plasma-		
60/390,183	6/21/2002	Polymerization Coating	N/A	NA
	·	Method for Eliminating Polycide		
		Voids Through Nitrogen		
		Implantation	N/A	NA
		Method for Reducing Dimensions		
10/465,848	6/20/2003	Between Patterns on a Photomask	N/A	NA
,		Method of Modulating Threshold		
10/417,105	4/17/2003	Voltage of a Mask ROM	N/A	NA
		Method for Forming Shallow		
		Trench Isolation With Control of		
10/385,483	3/12/2003	Bird Beak	N/A	NA
······································		Method for Plymer Removal After		
10/376,229	3/3/2003	an Etching Process	N/A	NA
· · · · · · · · · · · · · · · · · · ·		Method for Shrinking Dimensions		
10/465,850	6/20/2003	of Photoresist	N/A	NA
	 	Method and System for		
		Lithography Using Phase-Change		
10/315,003	12/10/2002	Material	N/A	NA